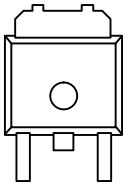
N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.016 @ V_{GS} = 10 V	40

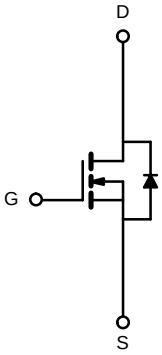
FEATURES

- TrenchFET® Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R_g Tested

TO-252



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 175°C)[b]	T_C = 25°C	I_D	40	A
	T_C = 125°C		30	
Pulsed Drain Current		I_{DM}	60	
Continuous Source Current (Diode Conduction)		I_S	40	
Avalanche Current		I_{AR}	40	
Repetitive Avalanche Energy (Duty Cycle ≤ 1%)	L = 0.1 mH	E_{AR}	80	mJ
Maximum Power Dissipation	T_C = 25°C	P_D	136[b]	W
	T_A = 25°C		3[a]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Junction-to-Case		R_{thJC}	0.85	1.1	

Notes
a. Surface Mounted on 1" x1" FR4 Board.
b. See SOA curve for voltage derating.

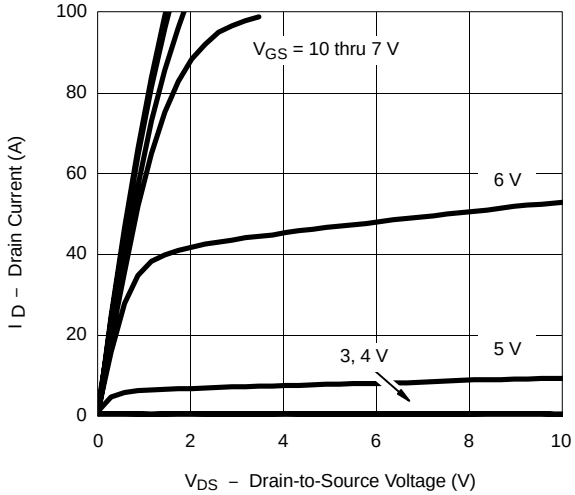
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0		4.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125°C			50	
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 175°C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	40			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 40 A		0.013	0.016	Ω
		V_{GS} = 10 V, I_D = 40 A, T_J = 125°C			0.027	
		V_{GS} = 10 V, I_D = 40 A, T_J = 175°C			0.037	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 40 A		45		S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, F = 1 MHz		1960		pF
Output Capacitance	C_{oss}			370		
Reverse Transfer Capacitance	C_{rss}			200		
Total Gate Charge[c]	Q_g	V_{DS} = 40 V, V_{GS} = 10 V, I_D = 40 A		42	60	nC
Gate-Source Charge[c]	Q_{gs}			7		
Gate-Drain Charge[c]	Q_{gd}			13		
Gate Resistance	R_g		0.5		2.7	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 40 V, R_L = 1.0 Ω I_D ≅ 40 A, V_{GEN} = 10 V, R_g = 2.5 Ω		12	20	ns
Rise Time[c]	t_r			52	80	
Turn-Off Delay Time[c]	$t_{d(off)}$			25	38	
Fall Time[c]	t_f			10	15	
Source-Drain Diode Ratings and Characteristic (T_C = 25°C)						
Pulsed Current	I_{SM}				40	A
Diode Forward Voltage[b]	V_{SD}	I_F = 40 A, V_{GS} = 0 V		1.0	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 40 A, di/dt = 100 A/µs		45	70	ns

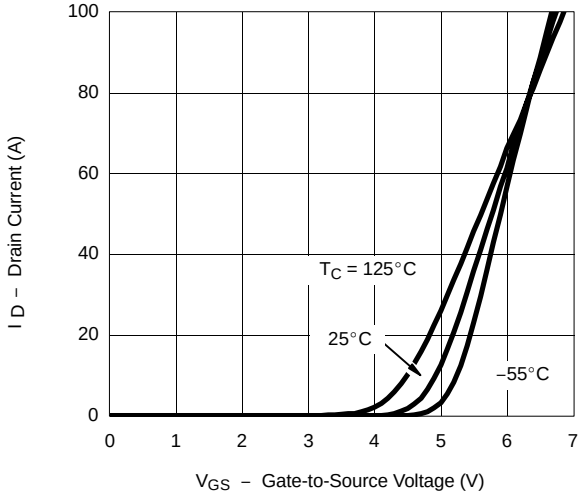
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

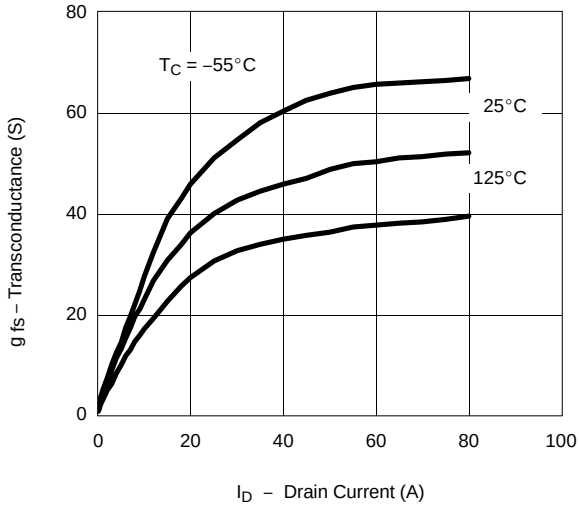
Output Characteristics



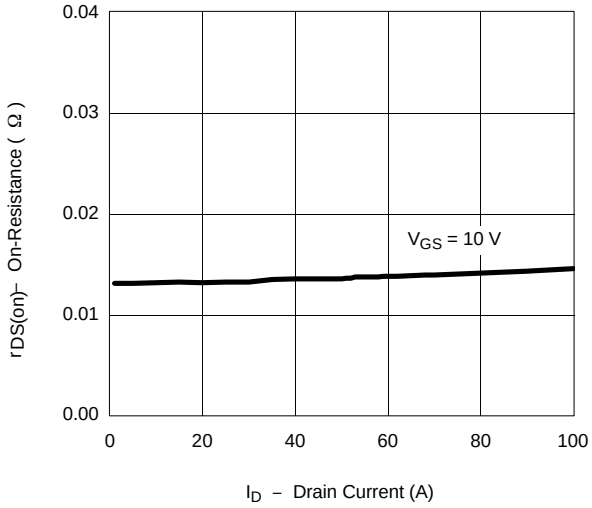
Transfer Characteristics



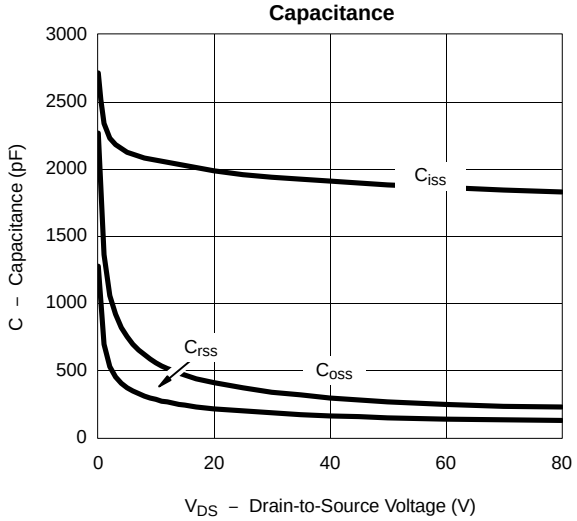
Transconductance



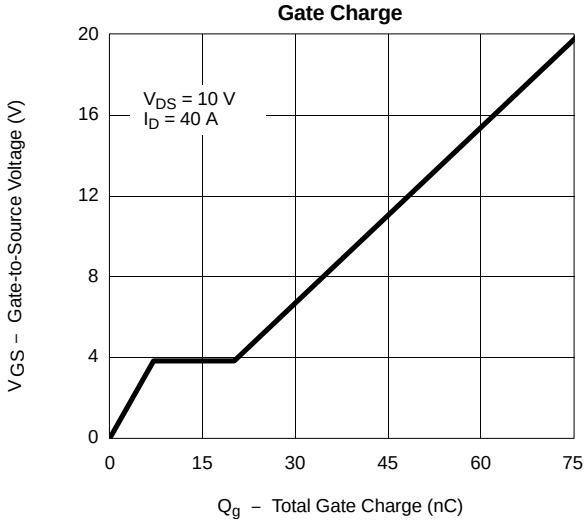
On-Resistance vs. Drain Current



Capacitance

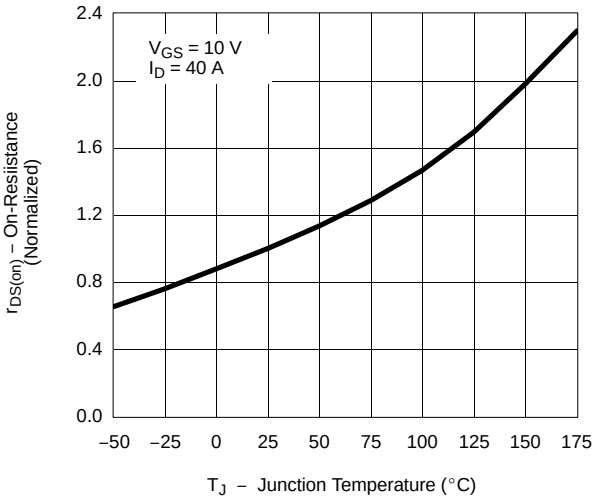


Gate Charge

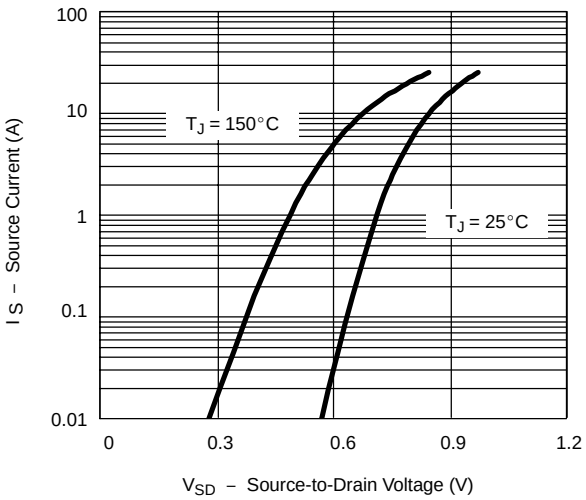


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

On-Resistance vs. Junction Temperature

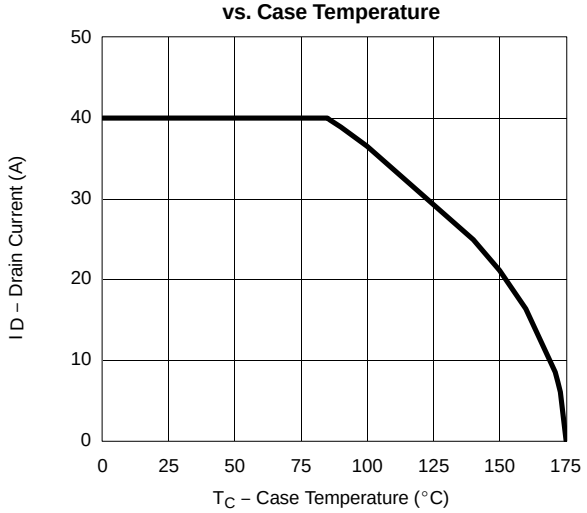


Source-Drain Diode Forward Voltage

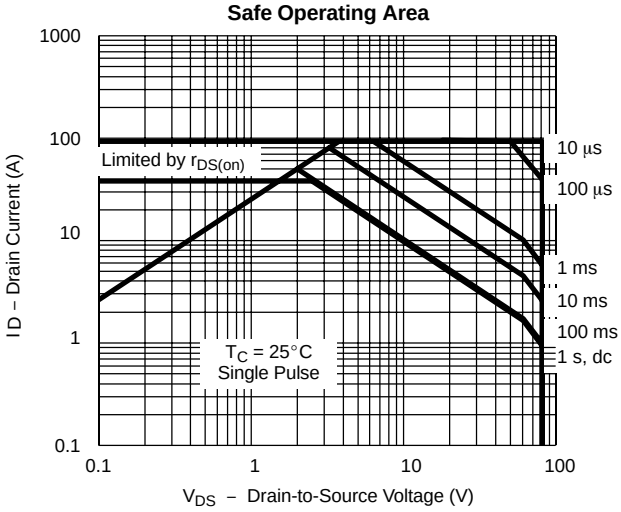


THERMAL RATINGS

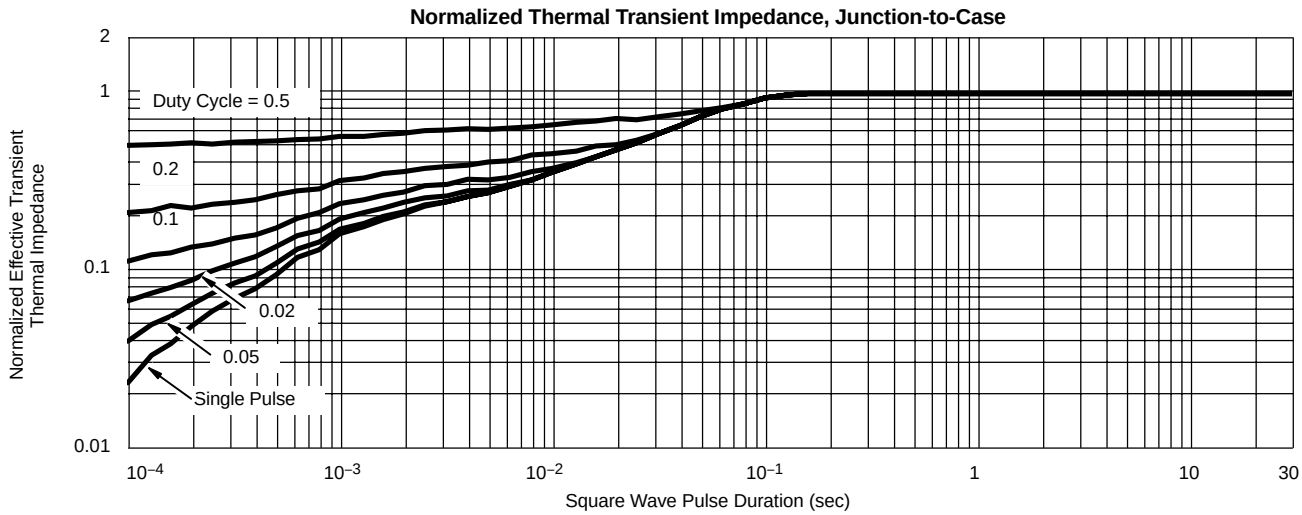
Maximum Avalanche Drain Current vs. Case Temperature



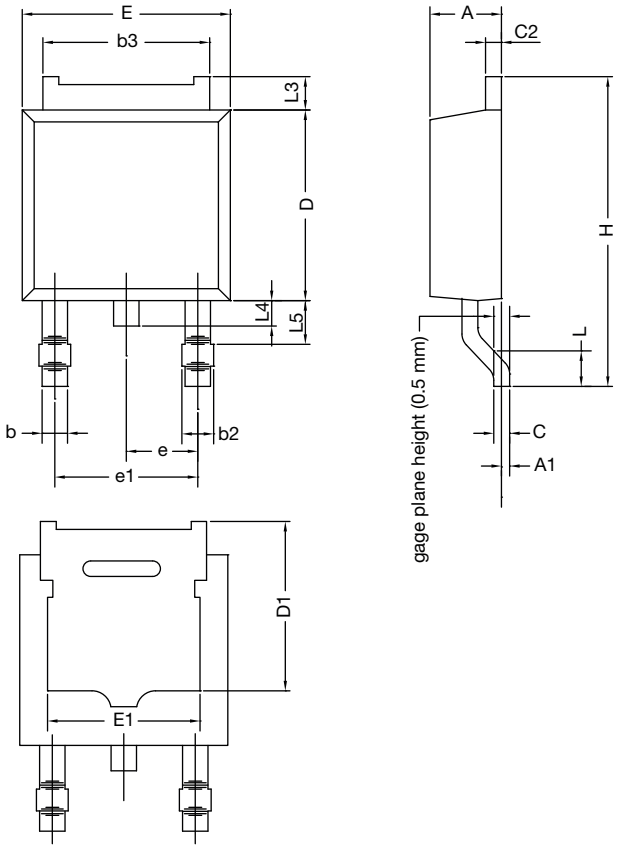
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE

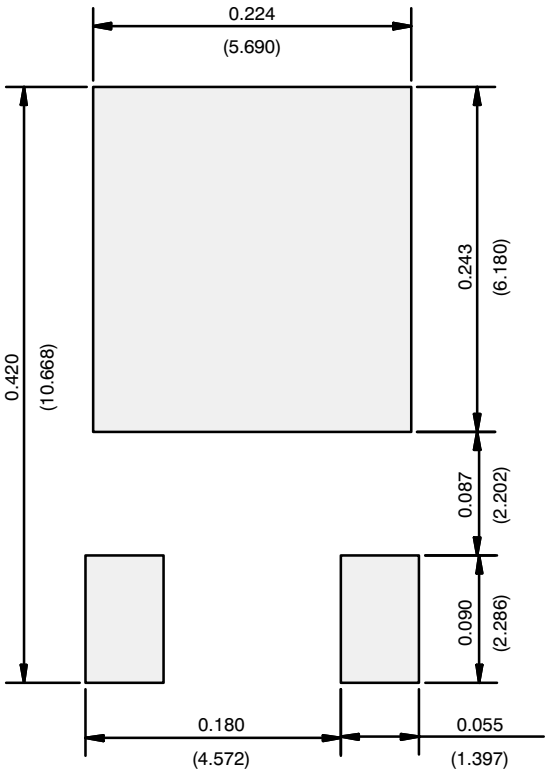


	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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